# High Speed Switching Transistor





#### **Features**

## RoHS Compliant

- NPN Silicon Planar Switching Transistor
- · Fast switching devices exhibiting short turn-off and low saturation voltage characteristics
- · Switching and Linear application DC and VHF Amplifier applications

### **Specification Table**

Vceo Max. (V)	Ic Max. (A)	VcE(sat) Max. (V) at Ic = 150mA	t <sub>Off</sub> Max. (ns) at Ic = 150mA	hfe Min. at Ic = 150mA	P <sub>tot</sub> at 25°C (mW)	Package and Pin Out
40	0.8	0.3	60	100	500	TO-18

### **Absolute Maximum Ratings**

Parameter	Symbol	Rating	Unit
Collector - Emitter Voltage	VCEO	40	
Collector - Base Voltage	Vсво	75	V
Emitter - Base Voltage	VEBO	6	
Collector Current Continuous	Ic	800	mA
Power Dissipation at T <sub>A</sub> = 25°C  Derate above 25°C	Pb	500 2.28	mW mW / °C
Power Dissipation at Tc = 25°C Derate above 25°C	Po	1.2 6.85	W mW / °C
Operating and Storage Junction Temperature Range	TJ, Tstg	-65 to +200	°C

### **Electrical Characteristics (TA = 25°C unless otherwise specified)**

Doromotor	Cumbal	Toot Condition	Value		
Parameter	Symbol	Test Condition	Minimum	Maximum	Unit
Collector - Emitter Voltage	VCEO	Ic = 10mA, I <sub>B</sub> = 0	40	-	
Collector - Base Voltage	Vсво	Ic = 10μA, Iε = 0	75	-	V
Emitter - Base Voltage	VEBO	Iε = 10μA, Ic = 0	6	-	
Collector Cut off Current	Ісво	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0 T <sub>A</sub> = 150°C		10	nA
Collector - Cut off Current	Icex	Vcb = 60V, IE = 0 Vce = 60V, Veb = 3V	-	10 10	μA nA
Emitter - Cut off Current	ІЕВО	V <sub>EB</sub> = 3V, I <sub>C</sub> = 0	-	10	n 1
Base - Cut off Current	IBL	Vce = 60V, Veb = 3V	-	20	nA
Collector Emit > 35 tor Coturation Voltage	*\/o= (Cat)	Ic = 150mA, IB = 15mA	-	0.3	
Collector Emit >35 ter Saturation Voltage	*Vce (Sat)	Ic = 500mA, IB = 50mA	-	1	V
Page Emitter Saturation Voltage	*\/p= (Cat)	Ic = 150mA, I <sub>B</sub> = 15mA	-	0.6 to 1.2	V
Base Emitter Saturation Voltage	*VBE (Sat)	Ic = 500mA, Iв = 50mA	-	2	

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### **Electrical Characteristics (TA = 25°C unless otherwise specified)**

Ic Ic Ic	c = 0.1mA, Vce = 10V c = 1mA, Vce = 10V	>35 >50 >75	
lc :	E = 10 mA, VCE = 10V TA = 55°C E = 10mA, VCE = 10V E = 150mA, VCE = 10V E = 150mA, VCE = 1V E = 500mA, VCE = 10V	>35 100 to 300 >50 >40	-

#### **Dynamic Characteristics**

		ALL F = 1kHz		
Small Signal Current Gain	hfE	Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V	50 to 300 75 to 375	-
Input Impedance	h⊫	Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V	2 to 8 0.25 to 1.25	kΩ
Voltage Feedback Ratio	hre	Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V	<8 <4	x10-4
Output Admittance	hoe	Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V	5 to 35 25 to 200	umhos
Collector Base Time Constant	rb'Cc	IE = 20mA, Vcв = 20V f = 31.8MHz	<150	ps

#### **Dynamic Characteristics**

Real Part Common - Emitter High Frequency	Re (hie)	Ic = 20mA, VcE = 20V	<60	Ω
Input Impedance	-	f = 300MHz	-	-
Noise Figure	Nf	Ic = 100μA, Vcε = 10V Rs = 1kΩ, f = 1kHz	<4	dB
Transistors Frequency	ft	Ic = 20mA, VcE = 20V f = 100MHz	>300	MHz
Output Capacitance	Cob	VcB = 10V, IE = 0 f = 100kHz	<8	, E
Input Capacitance	Cib	V <sub>EB</sub> = 0.5V, I <sub>C</sub> = 0 f = 100kHz	<25	pF

#### **Switching Time**

Delay Time	td	Ic = 150mA, IB1 = 15mA	<10	
Rise Time	tr	Vcc = 30V, VBE = 0.5V	<25	
Storage Time	ts	Ic = 150mA, IB1 =	<225	ns
Fall Time	tr	IB2 = 15mA, Vcc = 30V	<60	

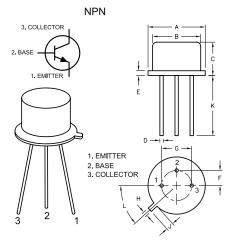
<sup>\*</sup>Pulse Condition: Pulse Width = 300µs, Duty Cycle = 2%



## **High Speed Switching Transistor**



#### **TO-18 Metal Can Package**



Dimensions	Minimum	Maximum
Α	5.24	5.84
В	4.52	4.97
С	4.31	5.33
D	0.4	0.53
E	-	0.76
F	-	1.27
G	-	2.97
Н	0.91	1.17
J	0.71	1.21
K	12.7	-
L	4	5°

Dimensions: Millimetres

Material content declaration of TO-18 1pc weight: 0.3092gm							
Components	Substance make up of Material	Chemical Composition	CAS Number	Amount of substances (gm)			
Header/cap	KOVAR, CRS1010	Fe Ni 29 Co 18 Glass	7439-89-6 7440-02-0 7440-48-4	0.2889gm			
Chip	Silicon	Si	7440-21-3	0.0031gm			
Bonding Wire	Aluminium (Al)	Al	7429-90-05	0.00089gm			
Tin Plating	Pure Tin	Sn	7440-31-5	0.0074gm			

#### **Part Number Table**

Description	Part Number
Bipolar (BJT) Single Transistor, NPN, 40V, 300MHz, 1.2W, 800mA	2N2222A

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Page <3>

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